

N-Channel 100 V (D-S) MOSFET

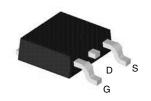
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^a		
100	$0.0068 \text{ at V}_{GS} = 10 \text{ V}$	90		
	0.0095 at $V_{GS} = 4.5 \text{ V}$	80		

FEATURES

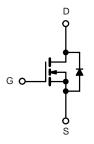
- 175 °C Junction Temperature
- TrenchFET® Power MOSFET
- Material categorization:



TO-252 Pin Configuration







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Gate-Source Voltage		V_{GS}	± 20	V		
Continuous Drain Current (T ₁ = 175 °C) ^b	T _C = 25 °C	,	90			
Continuous Diam Current (1) = 175 °C)	T _C = 100 °C	I _D	80 ^a			
Pulsed Drain Current	I _{DM}	330	Α			
Continuous Source Current (Diode Conduction)	I _S	80 ^a				
Avalanche Current	I _{AS}	80				
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AS}	125	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	136	W		
Maximum Fower Dissipation	T _A = 25 °C	' D	3 ^b , 8.3 ^{b, c}			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maniana la satisma ta Amelianta	t ≤ 10 sec	Р	15	18	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	40	50		
Maximum Junction-to-Case		R _{thJC}	0.85	1.1		

Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $c.\ t \leq 10\ s.$





SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol Test Conditions Min.		Typ. ^a	Max.	Unit		
Static	•		l	•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ 100				V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	2	3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	90			Α	
		V _{GS} = 10 V, I _D = 20 A		0.0068	0.0085	Ω	
D : 0	D	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0140		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0180		
		V _{GS} = 4.5 V, I _D = 15 A		0.0095	0.0120		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		50		S	
Dynamic							
Input Capacitance	C _{iss}			4150			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		420		pF	
Reverse Transfer Capacitance	C _{rss}			35		1	
Total Gate Charge ^c	Q_g			47	70		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$		15		nC	
Gate-Drain Charge ^c	Q_{gd}			10			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, R}_{L} = 0.6 \Omega$		10	20	no	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		35	50	ns	
Fall Time ^c	t _f			6	10		
Source-Drain Diode Ratings and Cha	aracteristics (T _C = 25 °C)			- 1		
Pulsed Current	I _{SM}				320	Α	
Diode Forward Voltage	V_{SD}	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs		85	110	ns	

Notes:

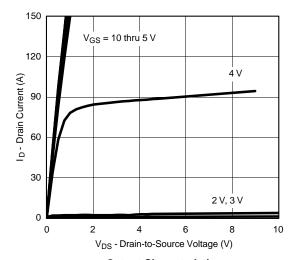
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

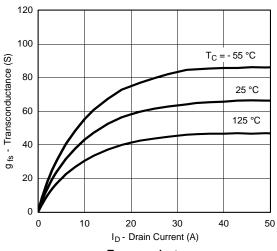




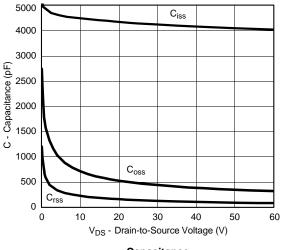
TYPICAL CHARACTERISTICS (25 °C unless noted)



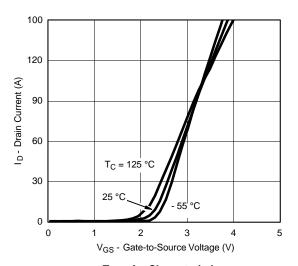
Output Characteristics



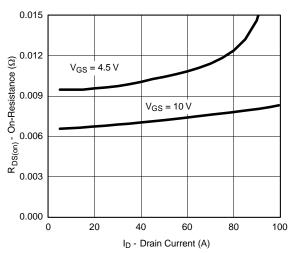
Transconductance



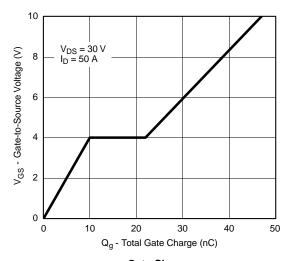
Capacitance



Transfer Characteristics



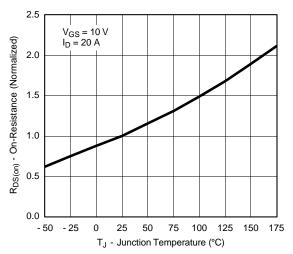
On-Resistance vs. Drain Current



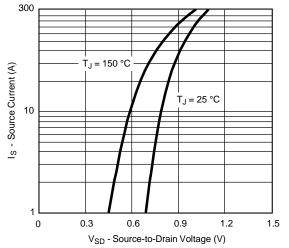
Gate Charge



TYPICAL CHARACTERISTICS (25 °C unless noted)



On-Resistance vs. Junction Temperature

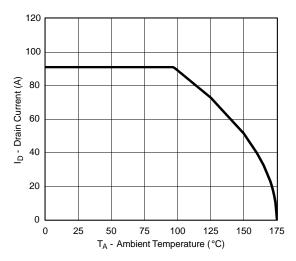


Source-Drain Diode Forward Voltage

THERMAL RATINGS

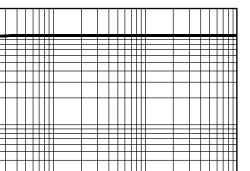
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1000 10 µs 100 100 µs I_D - Drain Current (A) R_{DS(on)}* 10 1 ms 10 ms 100 ms DC T_C = 25 °C Single Pulse 0.1 0.01 - 0.1 100 $V_{DS} - Drain-to-Source \ Voltage \ (V) \\ ^*V_{GS} > minimum \ V_{GS} \ at \ which \ R_{DS(on)} \ is \ specified$ Safe Operating Area

Maximum Drain Current vs. Ambient Temperature

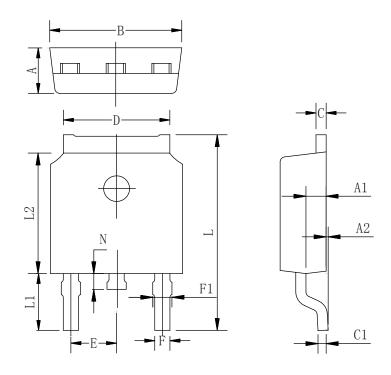


Duty Cycle = 0.5 Normalized Effective Transient Thermal Impedance 0.2 0.1 0.05 0.02 Single Pulse 0.01 10-4 10-3 10-2 10-1 10 100 Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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